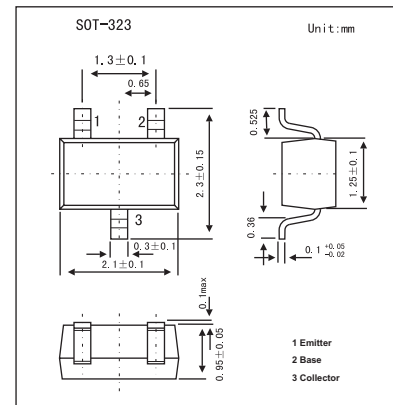


High-frequency Amplifier Transistor

2SC4098

■ Features

- Low collector capacitance. (Cob : Typ. 1.3pF)
- Low rbb, high gain, and excellent noise characteristics.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	40	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	50	mA
Collector power dissipation	P _C	0.2	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	BV _{CB0}	I _C =50μA	40			V
Collector-emitter voltage	BV _{CEO}	I _C =1mA	25			V
Emitter-base voltage	BV _{EB0}	I _E =50μA	5			V
Collector cutoff current	I _{CB0}	V _{CB} =24V			0.5	μA
Emitter cutoff current	I _{EB0}	V _{EB} =3V			0.5	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C /I _B =10mA/1mA		0.1	0.3	V
Forward current transfer ratio	h _{FE}	V _{CE} =6V, I _C =1mA	82		180	
Transition frequency	f _T	V _{CE} =6V, I _E =-1mA, f=100MHz	150	300		MHz
Output capacitance	C _{ob}	V _{CB} =6V, I _E =0A, f=1MHz		1.3	2.2	pF

■ Marking

Marking	AP